

GAN041-650WSB 650 V, 35 mΩ Gallium Nitride (GaN) FET in a TO-247 package 12 January 2021 Product data shee Product data sheet

1. General description

The GAN041-650WSB is a 650 V. 35 mΩ Gallium Nitride (GaN) FET in a TO-247 package. It is a normally-off device that combines Nexperia's latest high-voltage GaN HEMT H2 technology and low-voltage silicon MOSFET technologies — offering superior reliability and performance.

2. Features and benefits

- Ultra-low reverse recovery charge
- Simple gate drive (0 V to +10 V or 12 V)
- Robust gate oxide (±20 V capability)
- High gate threshold voltage (+4 V) for very good gate bounce immunity
- Very low source-drain voltage in reverse conduction mode
- Transient over-voltage capability

3. Applications

- Hard and soft switching converters for industrial and datacom power
- Bridgeless totempole PFC
- PV and UPS inverters
- Servo motor drives

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	-55 °C ≤ T _j ≤ 175 °C	-	-	650	V
ID	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	47.2	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	187	W
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics		I			
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 32 A; T _j = 25 °C; Fig. 11	-	35	41	mΩ
Dynamic ch	naracteristics		I			
Q _{GD}	gate-drain charge	I _D = 32 A; V _{DS} = 400 V; V _{GS} = 10 V;	-	6.6	-	nC
Q _{G(tot)}	total gate charge	T _j = 25 °C; <u>Fig. 13;</u> <u>Fig. 14</u>	-	22	-	nC
Source-dra	in diode		· · · · ·			
Qr	recovered charge	I_{S} = 32 A; dI _S /dt = -1000 A/µs; V _{GS} = 0 V; V _{DS} = 400 V; <u>Fig. 20</u>	-	150	-	nC

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5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	S	source		
3	D	drain		
mb	S	mounting base; connected to source	TO-247 (SOT429)	G aaa-028116

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
GAN041-650WSB	TO-247	plastic, single-ended through-hole package; 3 leads; 5.45 mm pitch; 20.45 mm x 15.6 mm x 4.95 mm body	SOT429				

7. Marking

Table 4. Marking codes				
Type number	Marking code			
GAN041-650WSB	GAN041 650WSB			

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

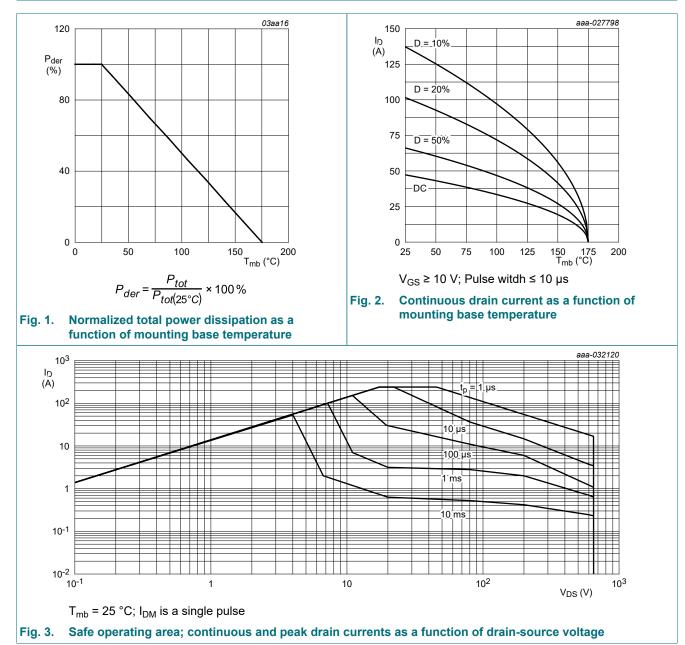
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	-55 °C ≤ T _j ≤ 175 °C	-	650	V
V _{TDS}	transient drain to source voltage	pulsed; $t_p = 1 \ \mu s$; $\delta_{factor} = 0.01$	-	725	V
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	187	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	47.2	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	-	33.4	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3	-	240	А
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C

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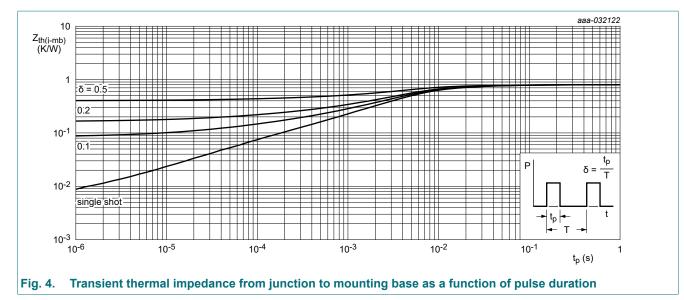
Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain diode						
I _S	source current	T _{mb} = 25 °C; V _{GS} = 0 V		-	47.2	A
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	240	A



9. Thermal characteristics

Table 6. The	Fable 6. Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4		-	-	0.8	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·	I			
V _{GS(th)}	gate-source threshold	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C	3.4	3.9	4.5	V
	voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 10</u>	2.2	-	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 10</u>	-	-	5.2	V
I _{DSS}	drain leakage current gate leakage current drain-source on-state resistance	V _{DS} = 650 V; V _{GS} = 0 V; T _j = 25 °C	-	2.5	25	μA
		V _{DS} = 650 V; V _{GS} = 0 V; T _j = 175 °C	-	20	-	μA
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	400	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	400	nA
R _{DSon}		V _{GS} = 10 V; I _D = 32 A; T _j = 25 °C; Fig. 11	-	35	41	mΩ
		V _{GS} = 10 V; I _D = 32 A; T _j = 175 °C; Fig. 12	-	84	98	mΩ
R _G	gate resistance	f = 1 MHz	0.8	1.9	4.8	Ω
Dynamic ch	aracteristics	· · ·				
Q _{G(tot)}	total gate charge	I _D = 32 A; V _{DS} = 400 V; V _{GS} = 10 V;	-	22	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	8.4	-	nC
Q _{GD}	gate-drain charge		-	6.6	-	nC
C _{iss}	input capacitance	V _{DS} = 400 V; V _{GS} = 0 V; f = 1 MHz;	-	1500	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	147	-	pF
C _{rss}	reverse transfer capacitance		-	5	-	pF
C _{o(er)}	effective output capacitance, energy related	$0 V \le V_{DS} \le 400 V; V_{GS} = 0 V;$ f = 1 MHz; T _j = 25 °C; <u>Fig. 16</u>	-	220	-	pF
C _{o(tr)}	effective output capacitance, time related	$0 V \le V_{DS} \le 400 V; V_{GS} = 0 V;$ f = 1 MHz; T _j = 25 °C	-	380	-	pF

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{d(on)}	turn-on delay time	V_{DS} = 400 V; R _L = 12.5 Ω; V _{GS} = 12 V;	-	14	-	ns
t _r	rise time	$R_{G(ext)} = 12 \Omega; I_S = 32 A; Fig. 17; Fig. 18$	-	14	-	ns
t _{d(off)}	turn-off delay time		-	36	-	ns
t _f	fall time		-	17	-	ns
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 400 V	-	150	-	nC
Source-dra	ain diode					
V _{SD}	source-drain voltage	I_{S} = 32 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 19</u>	-	1.8	-	V
		I _S = 16 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 19</u>	-	1.3	-	V
t _{rr}	reverse recovery time	I _S = 32 A; dI _S /dt = -1000 A/μs;	-	59	-	ns
Q _r	recovered charge	V _{GS} = 0 V; V _{DS} = 400 V; <u>Fig. 20</u>	-	150	-	nC

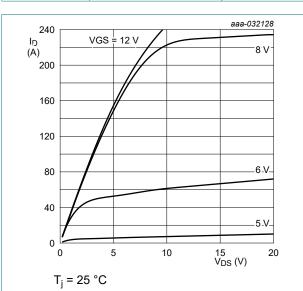
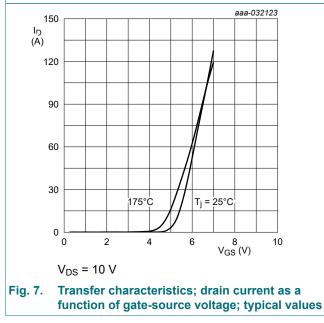
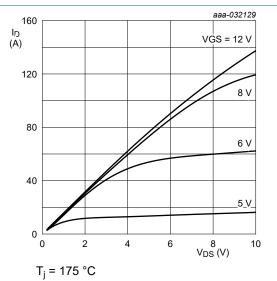
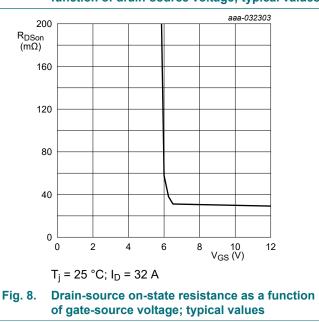


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values



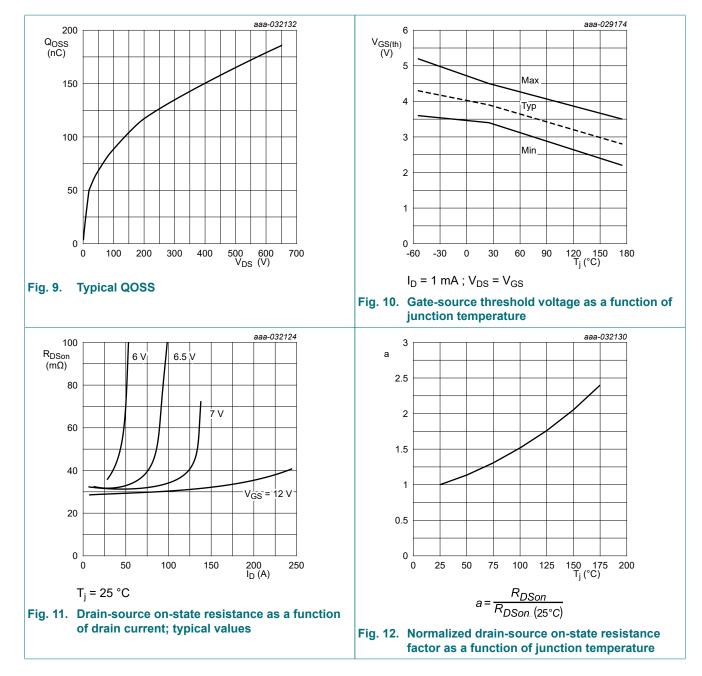




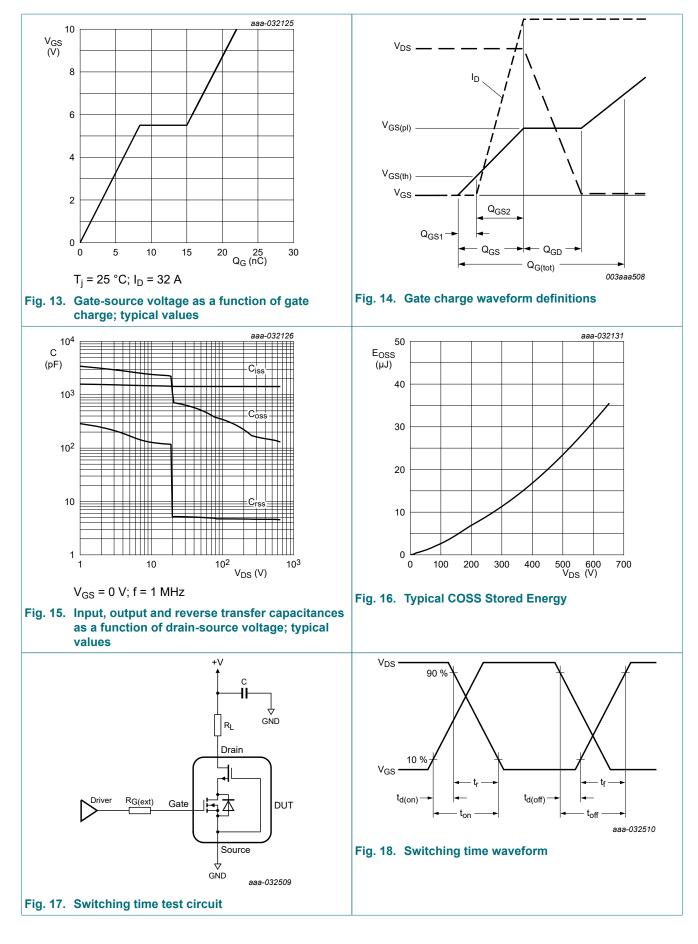


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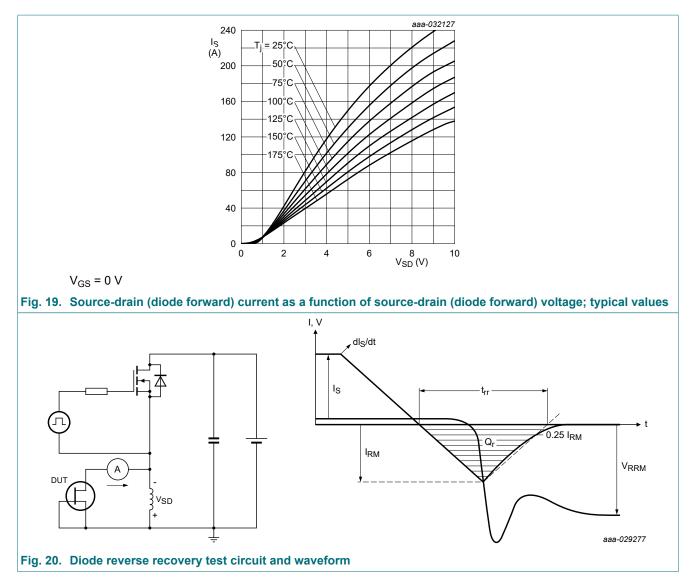
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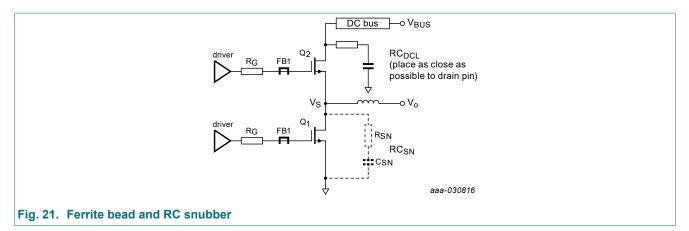
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11. Application information

A Ferrite bead must be fitted in series with the gate of the GaN FET and should be located as close as possible to the gate pin, (see figure below). Keeping the gate-source loop as compact as possible minimizes the gate loop inductance. The Ferrite bead damps the resonant circuit made up of the gate source loop inductance and the GaN FET input capacitance, thus providing fast switching stability. It is recommended that the impedance of the ferrite bead should be $200 \ \Omega - 270 \ \Omega \ (m) \ 100 \ MHz$, (recommended p/n BLM18AG221SN1D).

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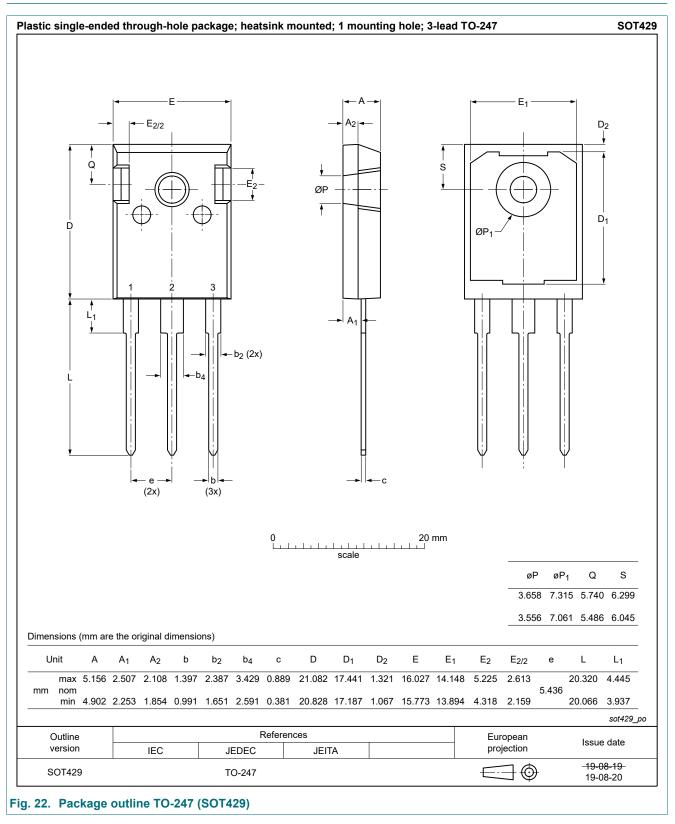


A DC-link snubber is recommended in all cases. Optimal is 20 nF in series with 4 Ω , most easily achieved with parallel combination 10 nF and 8 Ω . This snubber lowers the Q factor of any resonance in the bus. That resonance will act as a load on the high gain amplifier that is the GaN FET and can lead to instability. For very high current, an RC snubber is recommended for the switching node. This will increase switching loss, so this is only recommended at high power levels where the losses are a very small percentage of the total power.

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12. Package outline



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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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